

Abstract

A method of forming a single sided conductor and a semiconductor device having the same is provided. The method includes providing a substrate having an opening. The opening exposes a sidewall and an opening base surface. A tilted mask layer is formed in the opening. The tilted mask layer exposes the sidewall and a portion of the opening base surface. A dielectric layer is formed on the exposed sidewall and the exposed opening base surface. Then, the tilted mask layer is removed, and a conductive layer is formed over the substrate.